



CYPRESS

CY74FCT2652T

8-Bit Registered Transceiver

Features

- Function and pinout compatible with FCT and F logic
- FCT-C speed at 5.4 ns max. (Com'1)
FCT-A speed at 6.3 ns max. (Com'1)
- 25Ω output series resistors to reduce transmission line reflection noise
- Reduced V_{OH} (typically = 3.3V) versions of equivalent FCT functions
- Edge-rate control circuitry for significantly improved noise characteristics
- Power-off disable feature
- Matched rise and fall times
- Fully compatible with TTL input and output logic levels
- Sink current 12 mA
Source current 15 mA
- ESD > 2000V
- Independent register for A and B buses
- Multiplexed real-time and stored data transfer
- Extended commercial temp. range of -40°C to $+85^{\circ}\text{C}$

Functional Description

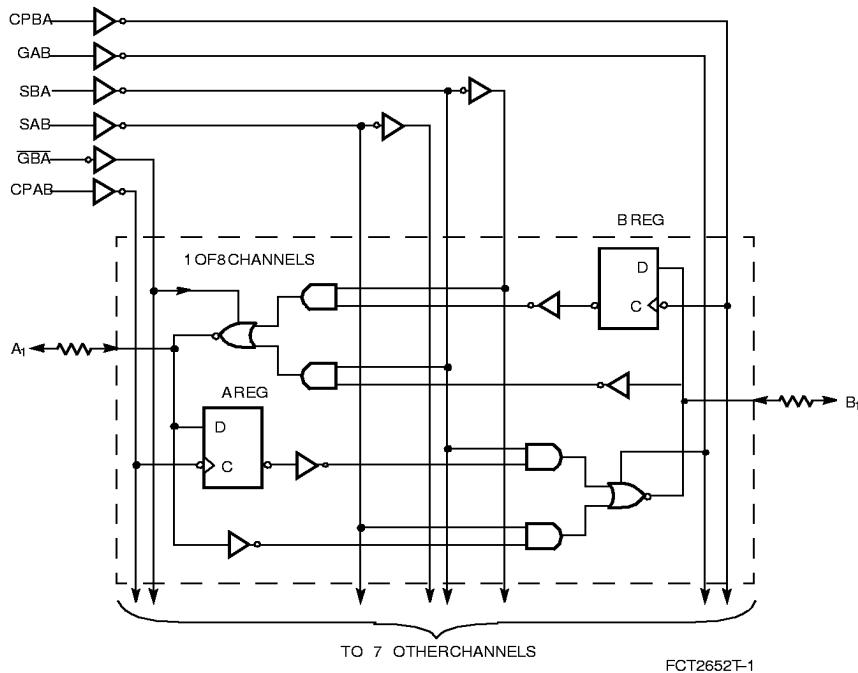
The FCT2652T consists of bus transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the input bus or from the internal storage registers. GAB and $\overline{\text{GBA}}$ control pins are provided to control the transceiver functions. SAB and SBA control pins are provided to select either real-time or stored data transfer.

The circuitry used for select control will eliminate the typical decoding glitch that occurs in a multiplexer during transition between stored and real-time data. A LOW input level selects real-time data and a HIGH selects stored data. Data on the A or B data bus, or both, can be stored in the internal D flip-flops by LOW-to-HIGH transitions at the appropriate clock pins (CPAB or CPBA), regardless of the select or enable control pins. When SAB and SBA are in the real-time transfer mode, it is also possible to store data without using the internal D-type flip-flops by simultaneously enabling GAB and $\overline{\text{GBA}}$. In this configuration, each output reinforces its input. Thus, when all other data sources to the two sets of bus lines are at high impedance, each set of bus lines will remain at its last state.

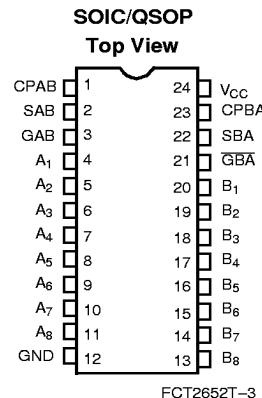
On-chip termination resistors are added to the outputs to reduce system noise caused by reflections. The FCT2652T can replace the FCT652T to reduce noise in existing designs.

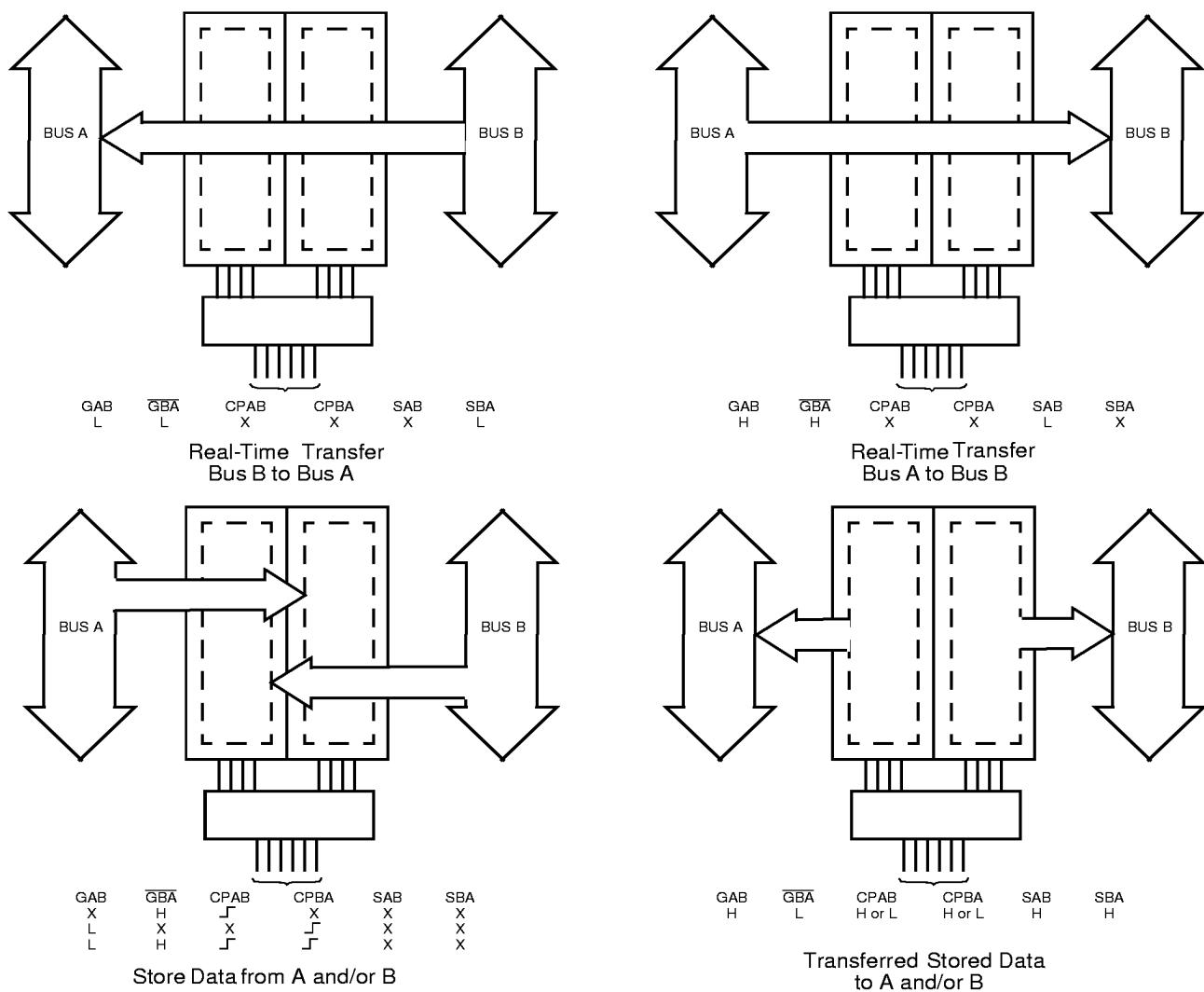
The outputs are designed with a power-off disable feature to allow for live insertion of boards

Logic Block Diagram



Pin Configurations




Function Table^[1]

Inputs						Data I/O		Operation or Function
GAB	GBA	CPAB	CPBA	SAB	SBA	A ₁ thru A ₈	B ₁ thru B ₈	
L	H	H or L	H or L	X	X	Input	Input	Isolation
L	H	✓	✓	X	X			Store A and B Data
X	H	✓	H or L	X ^[1]	X	Input	Unspecified ^[2]	Store A, Hold B
H	H	✓	✓	X ^[1]	X	Input	Output	Store A in both registers
L	X	H or L	✓	X	X	Unspecified ^[2]	Input	Hold A, Store B
L	L	✓	✓	X	X	Output	Input	Store B in both registers
L	L	X	H or L	X	L	Output	Input	Real-Time B Data to A Bus
L	L	X	H or L	X	H			Stored B Data to A Bus
H	H	X	H or L	X	X	Input	Output	Real-Time A Data to B Bus
H	H	X	H or L	X	X			Stored A Data to B Bus
H	L	H or L	H or L	H	H	Output	Output	Stored A Data to B Bus and Stored B Data to A Bus

Notes:

1. Select control=L: clocks can occur simultaneously.
Select control=H: clocks must be staggered in order to load both registers. H = HIGH Voltage Level. L = LOW Voltage Level. X = Don't Care.

Maximum Ratings^[3, 4]

(Above which the useful life may be impaired. For user guidelines, not tested.)	
Storage Temperature	−65°C to +150°C
Ambient Temperature with Power Applied	−65°C to +135°C
Supply Voltage to Ground Potential	−0.5V to +7.0V
DC Input Voltage	−0.5V to +7.0V
DC Output Voltage	−0.5V to +7.0V

DC Output Current (Maximum Sink Current/Pin	120 mA
Power Dissipation	0.5W
Static Discharge Voltage (per MIL-STD-883, Method 3015)	>2001V

Operating Range

Range	Ambient Temperature	V _{CC}
Commercial	−40°C to +85°C	5V ± 5%

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	Min.	Typ. ^[5]	Max.	Unit
V _{OH}	Output HIGH Voltage	V _{CC} =Min., I _{OH} =−15 mA	2.4	3.3		V
V _{OL}	Output LOW Voltage	V _{CC} =Min., I _{OL} =12 mA		0.3	0.55	V
R _{OUT}	Output Resistance	V _{CC} =Min., I _{OL} =12 mA	20	25	40	W
V _{IH}	Input HIGH Voltage		2.0			V
V _{IL}	Input LOW Voltage			0.8		V
V _H	Hysteresis ^[6]	All inputs		0.2		V
V _{IK}	Input Clamp Diode Voltage	V _{CC} =Min., I _{IN} =−18 mA		−0.7	−1.2	V
I _{IH}	Input HIGH Current	V _{CC} =Max., V _{IN} =V _{CC}			5	μA
I _{IH}	Input HIGH Current	V _{CC} =Max., V _{IN} =2.7V			±1	μA
I _{IL}	Input LOW Current	V _{CC} =Max., V _{IN} =0.5V			±1	μA
I _{OZH}	Off State HIGH-Level Output Current	V _{CC} =Max., V _{OUT} =2.7V			10	μA
I _{OZL}	Off State LOW-Level Output Current	V _{CC} =Max., V _{OUT} =0.5V			−10	μA
I _{OS}	Output Short Circuit Current ^[7]	V _{CC} =Max., V _{OUT} =0.0V	−60	−120	−225	mA
I _{OFF}	Power-Off Disable	V _{CC} =0V, V _{OUT} =4.5V			±1	μA

Capacitance^[6]

Parameter	Description	Test Conditions	Typ. ^[5]	Max.	Unit
C _{IN}	Input Capacitance		5	10	pF
C _{OUT}	Output Capacitance		9	12	pF

Notes:

- The data output functions may be enabled or disabled by various signals at the GAB or GBA inputs. Data input functions are always enabled, i.e., data at the bus pins will be stored on every LOW-to-HIGH transition on the clock inputs.
- Unless otherwise noted, these limits are over the operating free-air temperature range.
- Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CC} or ground.
- Typical values are at V_{CC}=5.0V, T_A=+25°C ambient.
- This parameter is guaranteed but not tested.
- Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample and hold techniques are preferable in order to minimize internal chip heating and more accurately reflect operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parametric tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

Power Supply Characteristics

Parameter	Description	Test Conditions	Typ. ^[5]	Max.	Unit
I_{CC}	Quiescent Power Supply Current	$V_{CC}=\text{Max.}, V_{IN} \leq 0.2V, V_{IN} \geq V_{CC}-0.2V$	0.1	0.2	mA
ΔI_{CC}	Quiescent Power Supply Current (TTL inputs HIGH)	$V_{CC}=\text{Max.}, V_{IN}=3.4V$ ^[8] $f_1=0$, Outputs Open	0.5	2.0	mA
I_{CCD}	Dynamic Power Supply Current ^[9]	$V_{CC}=\text{Max.}, \text{One Input Toggling, 50\% Duty Cycle, Outputs Open, GAB=GND, } \overline{GBA}=GND, V_{IN} \leq 0.2V \text{ or } V_{IN} \geq V_{CC}-0.2V$	0.06	0.12	mA/MHz
I_C	Total Power Supply Current ^[10]	$V_{CC}=\text{Max.}, f_0=10 \text{ MHz, 50\% Duty Cycle, Outputs Open, One Bit Toggling at } f_1=5 \text{ MHz, GAB=GND, } \overline{GBA}=GND, SAB=CPAB=GND, SBA=V_{CC}, V_{IN} \leq 0.2V \text{ or } V_{IN} \geq V_{CC}-0.2V$	0.7	1.4	mA
		$V_{CC}=\text{Max.}, f_0=10 \text{ MHz, 50\% Duty Cycle, Outputs Open, One Bit Toggling at } f_1=5 \text{ MHz, GAB=GND, } \overline{GBA}=GND, SAB=CPAB=GND, SBA=V_{CC}, V_{IN}=3.4V \text{ or } V_{IN}=GND$	1.2	3.4	mA
		$V_{CC}=\text{Max.}, f_0=10 \text{ MHz, 50\% Duty Cycle, Outputs Open, Eight Bits Toggling at } f_1=5 \text{ MHz, GAB= } \overline{GBA}=GND, SAB=CPAB=GND, SBA=V_{CC}, V_{IN} \leq 0.2V \text{ or } V_{IN} \geq V_{CC}-0.2V$	2.8	5.6 ^[11]	mA
		$V_{CC}=\text{Max.}, f_0=10 \text{ MHz, 50\% Duty Cycle, Outputs Open, Eight Bits Toggling at } f_1=5 \text{ MHz, GAB= } \overline{GBA}=GND, SAB=CPAB=GND, SBA=V_{CC}, V_{IN}=3.4V \text{ or } V_{IN}=GND$	5.1	14.6 ^[11]	mA

Notes:

8. Per TTL driven input ($V_{IN}=3.4V$); all other inputs at V_{CC} or GND.
9. This parameter is not directly testable, but is derived for use in Total Power Supply calculations.
10. $I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$
 $I_C = I_{CC} + \Delta I_{CC} D_H N_T + I_{CCD} (f_0/2 + f_1 N_1)$
 $I_{CC} = \text{Quiescent Current with CMOS input levels}$
 $\Delta I_{CC} = \text{Power Supply Current for a TTL HIGH input } (V_{IN}=3.4V)$
 $D_H = \text{Duty Cycle for TTL inputs HIGH}$
 $N_T = \text{Number of TTL inputs at } D_H$
 $I_{CCD} = \text{Dynamic Current caused by an input transition pair (HLH or LHL)}$
 $f_0 = \text{Clock frequency for registered devices, otherwise zero}$
 $f_1 = \text{Input signal frequency}$
 $N_1 = \text{Number of inputs changing at } f_1$
- All currents are in millamps and all frequencies are in megahertz.
11. Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.

Switching Characteristics^[12] Over the Operating Range^[13]

Parameter	Description	CY74FCT2652T		CY74FCT2652AT		CY74FCT2652CT		Unit	Fig. No.^[14]
		Min.	Max.	Min.	Max.	Min.	Max.		
t_{PLH} t_{PHL}	Propagation Delay Bus to Bus	1.5	9.0	1.5	6.3	1.5	5.4	ns	1, 3
t_{PZH} t_{PZL}	Output Enable Time En- able to Bus	1.5	14.0	1.5	9.8	1.5	7.8	ns	1, 7, 8
t_{PHZ} t_{PLZ}	Output Disable Time En- able to Bus	1.5	9.0	1.5	6.3	1.5	6.3	ns	1, 7, 8
t_{PLH} t_{PHL}	Propagation Delay Clock to Bus	1.5	9.0	1.5	6.3	1.5	5.7	ns	1, 5
t_{PLH} t_{PHL}	Propagation Delay SBA or SAB to A or B	1.5	11.0	1.5	7.7	1.5	6.2	ns	1, 5
t_S	Set-Up Time HIGH or LOW Bus to Clock	4.0		2.0		2.0		ns	4
t_H	Hold Time HIGH or LOW Bus to Clock	2.0		1.5		1.5		ns	4
t_W	Clock Pulse Width, ^[15] HIGH or LOW	6.0		5.0		5.0		ns	5

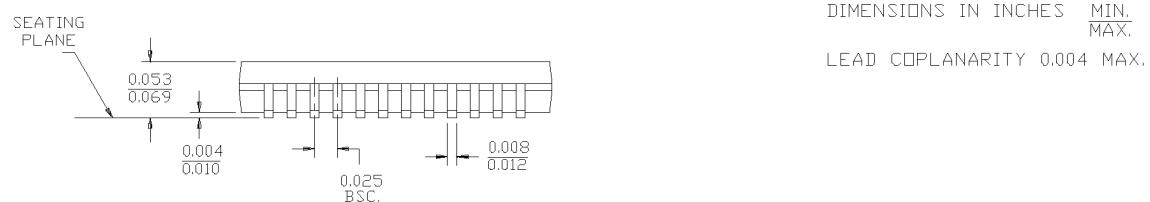
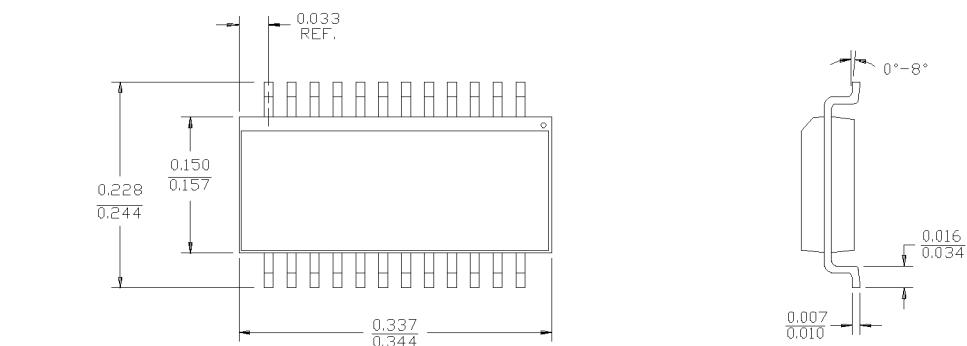
Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
5.4	CY74FCT2652CTQC	Q13	24-Lead (150-Mil) QSOP	Commercial
	CY74FCT2652CTSOC	S13	24-Lead (300-Mil) Molded SOIC	
6.3	CY74FCT2652ATQC	Q13	24-Lead (150-Mil) QSOP	Commercial
	CY74FCT2652ATSOC	S13	24-Lead (300-Mil) Molded SOIC	
9.0	CY74FCT2652TQC	Q13	24-Lead (150-Mil) QSOP	Commercial
	CY74FCT2652TSOC	S13	24-Lead (300-Mil) Molded SOIC	

Notes:

12. AC Characteristics guaranteed with $C_L=50\text{ pF}$ as shown in Figure 1 in "Parameter Measurement Information" in the General Information section.
13. Minimum limits are guaranteed but not tested on Propagation Delays.
14. See "Parameter Measurement Information" in the General Information section.
15. With one data channel toggling, $t_W(L)=t_W(H)=4.0\text{ ns}$ and $t_f=t_i=1.0\text{ ns}$.

Document #: 38-00344-B

Package Diagrams
24-Lead Quarter Size Outline Q13

24-Lead (300-Mil) Molded SOIC S13
